

The listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Previously Presented) A semiconductor device comprising:

at least one transistor;

at least one interlayer insulating film formed over said transistor, said interlayer insulating film having at least one contact hole;

an embedded conductive layer provided to fill said contact hole wherein a top surface of said embedded conductive layer is flush with a top surface of said interlayer insulating film; and

a reflective pixel electrode formed on said interlayer insulating film wherein said reflective pixel electrode is electrically connected to said transistor through said embedded conductive layer,

wherein the embedded conductive layer comprises a conductive material dispersed in a medium, the conductive material being selected from the group consisting of carbon, zinc oxide, aluminum, and nickel.

2. (Previously Presented) A semiconductor device comprising:

at least one transistor;

at least one interlayer insulating film comprising an organic resin formed over said transistor, said interlayer insulating film having at least one contact hole;

an embedded conductive layer provided to fill said contact hole wherein a top surface of said embedded conductive layer is flush with a top surface of said interlayer insulating film; and

a reflective pixel electrode formed on said interlayer insulating film wherein said reflective pixel electrode is electrically connected to said transistor through said embedded conductive layer,

wherein the embedded conductive layer comprises a conductive material dispersed in a medium, the conductive material being selected from the group consisting of carbon, zinc oxide, aluminum, and nickel.

3. (Previously Presented) A semiconductor device comprising:

at least one transistor;

a first interlayer insulating film formed over said transistor;

a drain electrode formed on said first interlayer insulating film and electrically connected to a drain of said transistor through an opening of said first interlayer insulating film;

a second interlayer insulating film formed over said drain electrode and said first interlayer insulating film;

a capacitor forming electrode formed on said second interlayer insulating film to form a capacitor between said drain electrode and said capacitor forming electrode;

a third interlayer insulating film formed over said capacitor forming electrode and said second interlayer insulating film;

a contact hole opened through said third and second interlayer insulating films to reach said drain electrode;

an embedded conductive layer filled in said contact hole; and

a reflective pixel electrode formed on said third interlayer insulating film, wherein said reflective pixel electrode is electrically connected to said drain electrode through said embedded conductive layer,

wherein the embedded conductive layer comprises a conductive material dispersed in a medium, the conductive material being selected from the group consisting of carbon, zinc oxide, aluminum, and nickel.

4. (Previously Presented) A semiconductor device comprising:

at least one transistor;

a first interlayer insulating film formed over said transistor;

a drain electrode formed on said first interlayer insulating film and electrically connected to a drain of said transistor through an opening of said first interlayer insulating film;

a second interlayer insulating film formed over said drain electrode and said first interlayer insulating film;

a capacitor forming electrode formed on said second interlayer insulating film to form a capacitor between said drain electrode and said capacitor forming electrode;

a third interlayer insulating film comprising an organic resin formed over said capacitor forming electrode and said second interlayer insulating film;

a contact hole opened through said third and second interlayer insulating films to reach said drain electrode;

an embedded conductive layer filled in said contact hole; and

a reflective pixel electrode formed on said third interlayer insulating film, wherein said reflective pixel electrode is electrically connected to said drain electrode through said embedded conductive layer,

wherein the embedded conductive layer comprises a conductive material dispersed in a medium, the conductive material being selected from the group consisting of carbon, zinc oxide, aluminum, and nickel.

5. (Previously Presented) A semiconductor device comprising:

at least one transistor;

a first interlayer insulating film comprising an organic resin formed over said transistor, said interlayer insulating film having at least one contact hole;

an embedded conductive layer provided to fill said contact hole wherein a top surface of said embedded conductive layer is flush with a top surface of said interlayer insulating film; and

a reflective pixel electrode formed on said interlayer insulating film wherein said reflective pixel electrode is electrically connected to said transistor through said embedded conductive layer, wherein said embedded conductive layer comprises a same resin as said resin of the interlayer insulating film.

6.-15. (Canceled)

16. (Currently Amended) A semiconductor device according to any one of claims 1 [[to 6]] and 47-50, further comprising an alignment film.

17.-21. (Canceled)

22. (Currently Amended) A semiconductor device according to claim 1, 2, 3, 4, 5, [[6,]] or 47-50 wherein said device is a display device of a cellular phone.

23. (Currently Amended) A semiconductor device according to claim 1, 2, 3, 4, 5, [[6,]] or 47-50 wherein said device is a display device of a camcorder.

24. (Currently Amended) A semiconductor device according to claim 1, 2, 3, 4, 5, [[6,]] or 47-50 wherein said device is a display device of a portable computer.

25. (Currently Amended) A semiconductor device according to claim 1, 2, 3, 4, 5, [[6,]] or 47-50 wherein said device is a display device of a head mounting display.

26. (Currently Amended) A semiconductor device according to claim 1, 2, 3, 4, 5, [[6,]] or 47-50 wherein said device is a display device of a rear type projector.

27. (Currently Amended) A semiconductor device according to claim 1, 2, 3, 4, 5, [[6,]] or 47-50 wherein said device is a display device of a front type projector.

28.-39. (Canceled)

40. (Currently Amended) A semiconductor device according to any one of claim 1 [[6,]] and 47-50 wherein said device is an EL display device.

41.-45. (Canceled)

46. (Previously Presented) The semiconductor device according to claim 5 wherein said third interlayer insulating film and said embedded conductive layer both comprises an acrylic resin.

47. (Previously Presented) A semiconductor device comprising:
at least one transistor;
at least one interlayer insulating film formed over said transistor, said interlayer insulating film having at least one contact hole;
an embedded conductive layer provided to fill said contact hole wherein a top surface of said embedded conductive layer is flush with a top surface of said interlayer insulating film; and
a reflective pixel electrode formed on said interlayer insulating film wherein said reflective pixel electrode is electrically connected to said transistor through said embedded conductive layer, wherein said embedded conductive layer comprises an indium tin oxide.

48. (Previously Presented) A semiconductor device comprising:

at least one transistor;

at least one interlayer insulating film comprising an organic resin formed over said transistor, said interlayer insulating film having at least one contact hole;

an embedded conductive layer provided to fill said contact hole wherein a top surface of said embedded conductive layer is flush with a top surface of said interlayer insulating film; and

a reflective pixel electrode formed on said interlayer insulating film wherein said reflective pixel electrode is electrically connected to said transistor through said embedded conductive layer,

wherein said embedded conductive layer comprises an indium tin oxide.

49. (Previously Presented) A semiconductor device comprising:

at least one transistor;

a first interlayer insulating film formed over said transistor;

a drain electrode formed on said first interlayer insulating film and electrically connected to a drain of said transistor through an opening of said first interlayer insulating film;

a second interlayer insulating film formed over said drain electrode and said first interlayer insulating film;

a capacitor forming electrode formed on said second interlayer insulating film to form a capacitor between said drain electrode and said capacitor forming electrode;

a third interlayer insulating film formed over said capacitor forming electrode and said second interlayer insulating film;

a contact hole opened through said third and second interlayer insulating films to reach said drain electrode;

an embedded conductive layer filled in said contact hole; and

a reflective pixel electrode formed on said third interlayer insulating film, wherein said reflective pixel electrode is electrically connected to said drain electrode through said embedded conductive layer,
wherein said embedded conductive layer comprises an indium tin oxide.

50. (Previously Presented) A semiconductor device comprising:

at least one transistor;

a first interlayer insulating film formed over said transistor;

a drain electrode formed on said first interlayer insulating film and electrically connected to a drain of said transistor through an opening of said first interlayer insulating film;

a second interlayer insulating film formed over said drain electrode and said first interlayer insulating film;

a capacitor forming electrode formed on said second interlayer insulating film to form a capacitor between said drain electrode and said capacitor forming electrode;

a third interlayer insulating film comprising an organic resin formed over said capacitor forming electrode and said second interlayer insulating film;

a contact hole opened through said third and second interlayer insulating films to reach said drain electrode;

an embedded conductive layer filled in said contact hole; and

a reflective pixel electrode formed on said third interlayer insulating film, wherein said reflective pixel electrode is electrically connected to said drain electrode through said embedded conductive layer,

wherein said embedded conductive layer comprises an indium tin oxide.

51. (Previously Presented) A device according to claim 1, wherein said medium is an organic material.

52. (Previously Presented) A device according to claim 2, wherein said medium is an organic material.

53. (Previously Presented) A device according to claim 3, wherein said medium is an organic material.

54. (Previously Presented) A device according to claim 4, wherein said medium is an organic material.

55. (Currently Amended) A device according to claim 47, wherein said medium is interlayer insulating film comprises an organic material.

56. (Currently Amended) A device according to claim 48, wherein said medium is interlayer insulating film comprises an organic material.

57. (Currently Amended) A device according to claim 49, wherein at least one of said ~~medium is~~ second and third interlayer insulating films comprises an organic material.

58. (Currently Amended) A device according to claim 50, wherein at least one of said ~~medium is~~ second and third interlayer insulating films comprises an organic material.

59. (Previously Presented) A device according to claim 1, wherein said medium is an inorganic material.

60. (Previously Presented) A device according to claim 2, wherein said medium is an inorganic material.

61. (Previously Presented) A device according to claim 3, wherein said medium is an inorganic material.

62. (Previously Presented) A device according to claim 4, wherein said medium is an inorganic material.

63. (Currently Amended) A device according to claim 47, wherein said ~~medium~~ is interlayer insulating film comprises an inorganic material.

64. (Currently Amended) A device according to claim 48, wherein said ~~medium~~ is interlayer insulating film comprises an inorganic material.

65. (Currently Amended) A device according to claim 49, wherein said ~~medium~~ is first interlayer insulating film comprises an inorganic material.

66. (Currently Amended) A device according to claim 50, wherein said ~~medium~~ is first interlayer insulating film comprises an inorganic material.

67. (Previously Presented) A device according to claim 1, wherein said interlayer insulating film comprises an organic material.

68. (Currently Amended) A device according to claim ~~[[3]]~~ 1, wherein said interlayer insulating film ~~is made from~~ comprises an inorganic material.

69. (Currently Amended) A device according to claim 3, wherein said interlayer insulating film ~~is made from~~ comprises an organic material.

70. (Currently Amended) A device according to claim 3, wherein said interlayer insulating film ~~is made from~~ comprises an inorganic material.

71. (Currently Amended) A device according to claim 47, wherein said interlayer insulating film ~~is made from~~ comprises an inorganic material.

72. (Currently Amended) A device according to claim 47, wherein said interlayer insulating film ~~is made from~~ comprises an organic material.

73. (Currently Amended) A device according to claim 49, wherein said interlayer insulating film ~~is made from~~ comprises an inorganic material.

74. (Currently Amended) A device according to claim 49, wherein said interlayer insulating film ~~is made from~~ comprises an organic material.